



DSS2540M

40V NPN LOW SATURATION TRANSISTOR IN X1-DFN1006-3

Features

- BVcEo > 40V
- Ic = 500mA High Collector Current
- Icm = 1A Peak Pulse Current
- P_D = 1000mW Power Dissipation
- Low Collector-Emitter Saturation Voltage, V_{CE(sat)}
- 0.60mm² Package Footprint, 13 Times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type DSS3540M
- Totally Lead Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

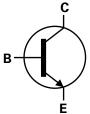
Package: X1-DFN1006-3

- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu.
 Solderable per MIL-STD-202, Method 208@4
- Weight: 0.0009 grams (Approximate)

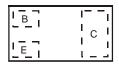




Bottom View



Device Symbol



Top View Device Schematic

Ordering Information (Note 4)

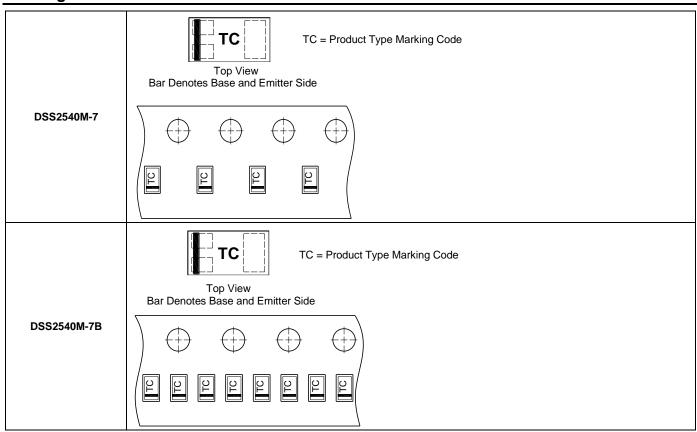
Orderable Part Number	Package	Marking Code Reel Siz	Reel Size (inches)	Tape Width (mm)	Pac	king
Orderable Part Number	Fackage	warking Code	Reel Size (Iliches)	rape widin (min)	Qty.	Carrier
DSS2540M-7	X1-DFN1006-3	TC	7	8mm	3,000	Reel
DSS2540M-7B	X1-DFN1006-3	TC	7	8mm	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	Vceo	40	V
Emitter-Base Voltage	VEBO	6	V
Collector Current - Continuous	Ic	500	mA
Peak Pulse Collector Current	Ісм	1	Α
Peak Base Current	I _{BM}	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	400	mW	
Fower Dissipation	(Note 6)	P _D	1000		
Thermal Resistance, Junction to Ambient	(Note 5)	2	310	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	RθJA	120		
Thermal Resistance, Junction to Lead (Note 7)		R _θ JL	120	°C/W	
Operating and Storage and Temperature Ran	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	В

Notes:

^{5.} For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.

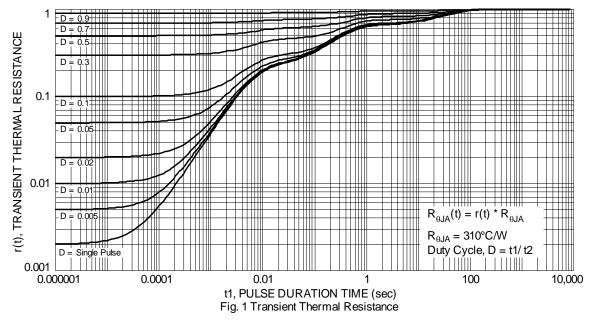
^{6.} Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.

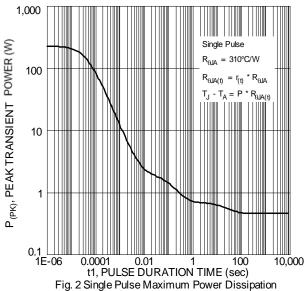
^{7.} Thermal resistance from junction to solder-point (on the exposed collector pad).

^{8.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics







Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	ВУсво	40		_	V	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	40		_	V	$I_C = 10mA, I_B = 0$
Emitter-Base Breakdown Voltage	BVEBO	6	_	_	V	$IE = 100\mu A, IC = 0$
Collector Cutoff Current	lone		_	100	nA	Vcb = 30V, IE = 0
Collector Cutoff Current	I _{CBO}			50	μΑ	$V_{CB} = 30V$, $I_E = 0$, $T_A = +150$ °C
Emitter Cutoff Current	IEBO	_	_	100	nA	$V_{EB} = 5V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)						
		200	_	_		VcE = 2V, Ic = 10mA
DC Current Gain	hFE	150	_	_	_	VcE = 2V, Ic = 100mA
		50	_			$V_{CE} = 2V, I_{C} = 500mA$
		_		50	mV	$I_C = 10mA, I_B = 0.5mA$
Collector-Emitter Saturation Voltage	V05()	_	_	100		$I_{C} = 100 \text{mA}, I_{B} = 5 \text{mA}$
Collector-Emitter Saturation Voltage	VCE(sat)	_	_	200		$I_C = 200 \text{mA}, I_B = 10 \text{mA}$
			_	250		Ic = 500mA, I _B = 50mA
Collector-Emitter Saturation Resistance	R _{CE(sat)}	1		500	mΩ	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}		_	1.2	V	Ic = 500mA, I _B = 50mA
Base-Emitter Turn On Voltage	V _{BE(on)}	_	_	1.1	V	Vce = 2V, Ic = 100mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	Cobo	_	_	6	pF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f⊤	250	300	_	MHz	VcE = 5V, Ic = 100mA, f = 100MHz

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

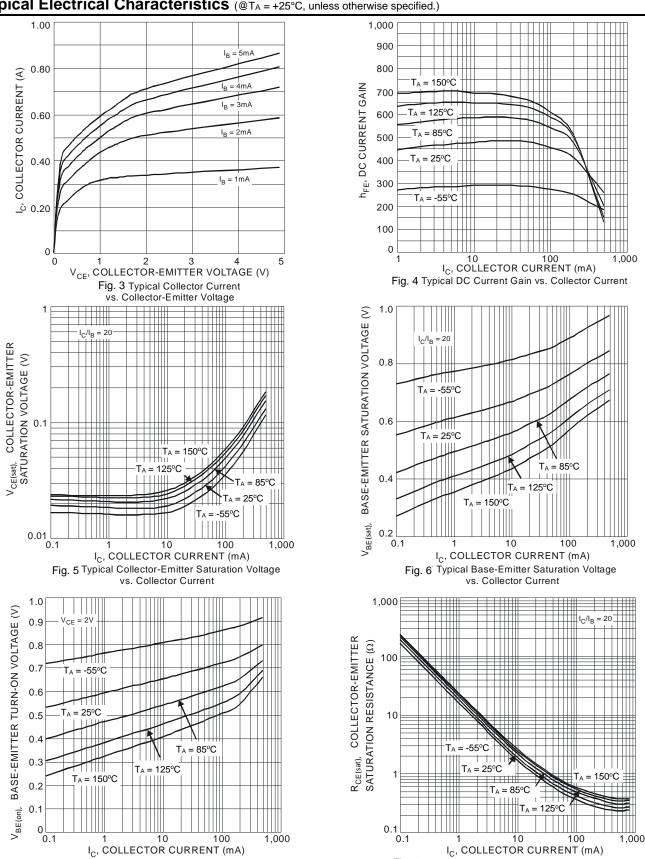


Fig. 7 Typical Base-Emitter Turn-On Voltage

vs. Collector Current

Fig. 8 Typical Collector-Emitter Saturation Resistance

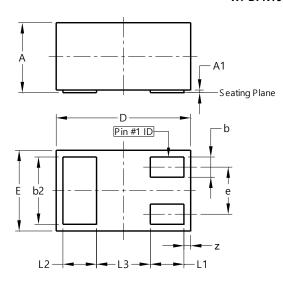
vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3

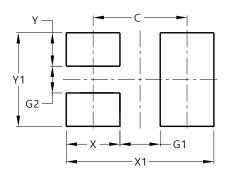


X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	•	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3



Dimensions	Value (in mm)		
С	0.70		
G1	0.30		
G2	0.20		
X	0.40		
X1	1.10		
Y	0.25		
Y1	0.70		



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